

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

TPD4EUSB30DQAR-MS

Product specification

Features

- 60Watts peak pulse power ($t_p = 8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j = 0.2pF$ typ. I/O to I/O)
- IEC 61000-4-2 $\pm 20kV$ contact $\pm 25kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20 μs)

Mechanical Data

- Molding compound flammability rating: UL94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

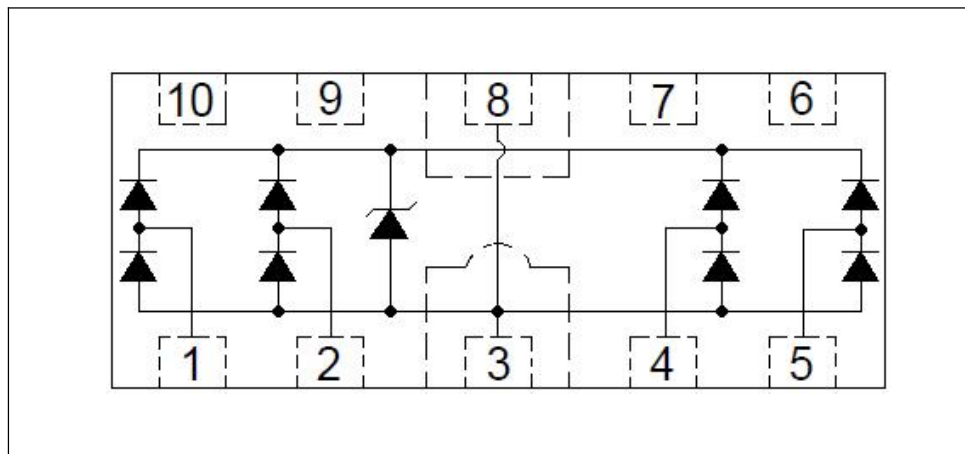
Applications

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3, eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

Reference News

PACKAGE OUTLINE	Marking
 DFN2510-10	

Schematic & PIN Configuration



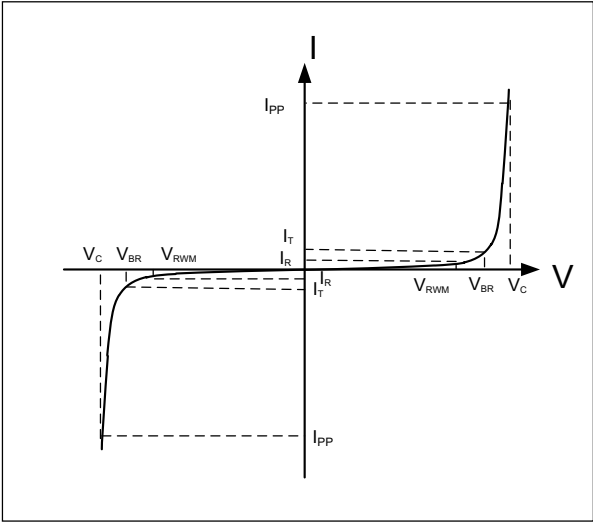
Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	6.0			V
Reverse Leakage Current	I_R	$V_{RWM}=5\text{V}, T=25^\circ\text{C}$			1	μA
Peak Pulse Current	I_{PP}	$t_p=8/20\mu\text{s}$			4	A
Clamping Voltage	V_C	$I_{PP}=4\text{A}, t_p=8/20\mu\text{s}$			15	V
Junction Capacitance	C_j	$V_R = 0\text{V}, f = 1\text{MHz}$ I/O to I/O		0.2	0.3	pF
		$V_R = 0\text{V}, f = 1\text{MHz}$ I/O to GND		0.4	0.55	

Electrical Parameters (TA = 25°C unless otherwise noted)

	Parameter
I_{PP}	MaximumReversePeak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	WorkingPeak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

Note: 8/20μs pulse waveform.



Typical Characteristic Curves

Fig.1 Peak Pulse Power Rating Curve

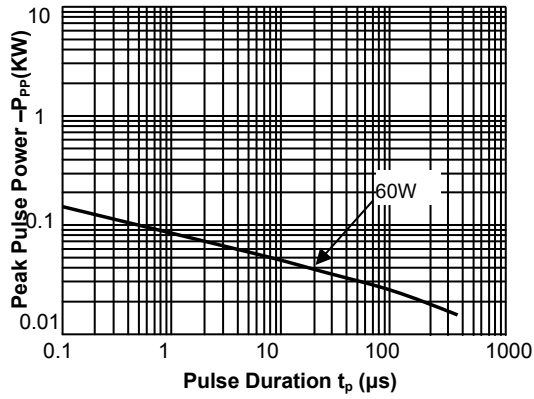


Fig.2 Pulse Derating Curve

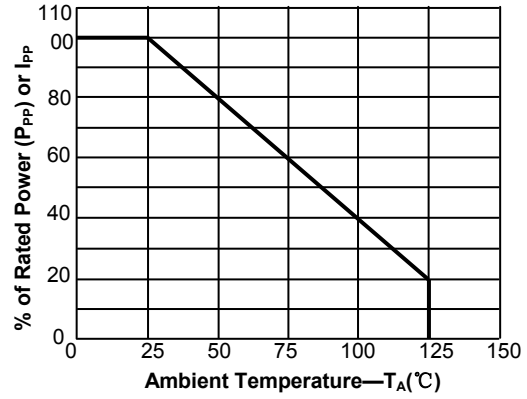


Fig.3 Pulse Waveform-8/20μs

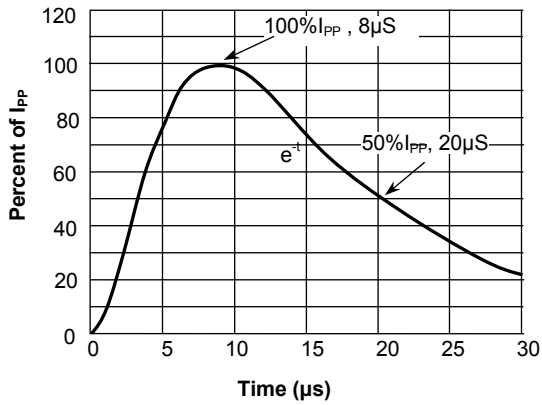
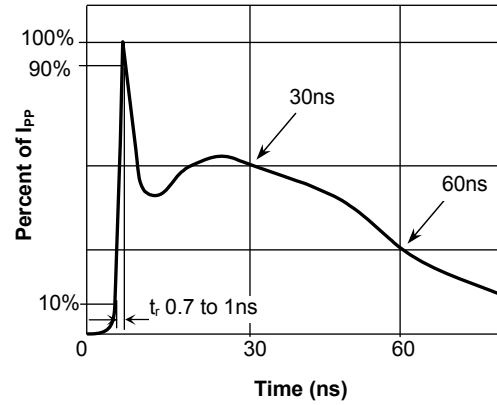
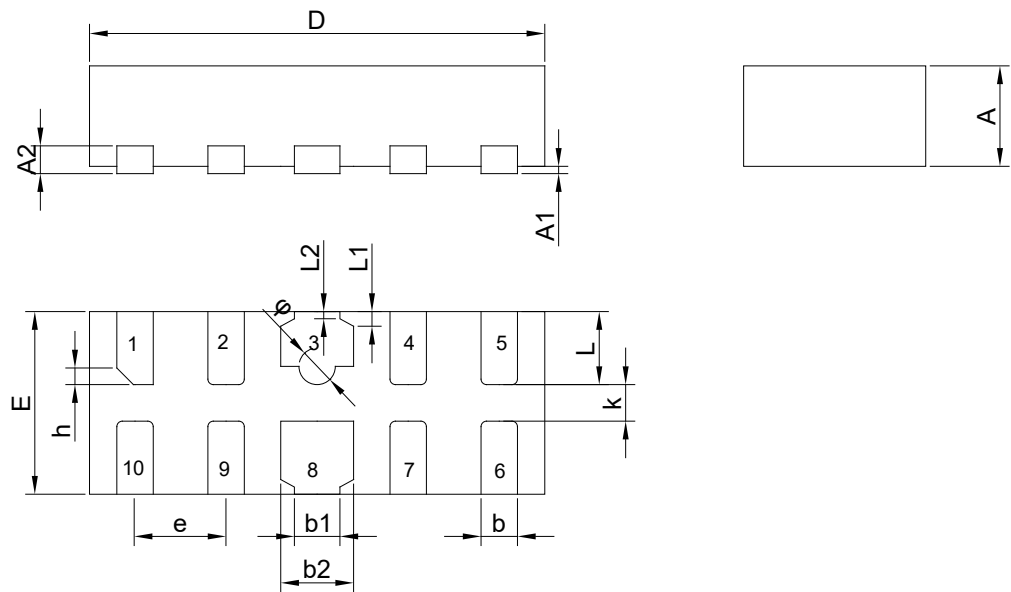


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)



Dimension (DFN2510-10)



Dimensions in Millimeter							
Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.500	0.550	0.600	D	2.450	2.500	2.550
A1	0.00	/	0.05	E	0.950	1.00	1.050
A2	0.122	0.152	0.200	e	0.450	0.500	0.550
b	0.150	0.200	0.250	h	0.080	0.120	0.150
b1	0.200	0.250	0.300	k	0.150	0.200	0.250
b2	0.350	0.400	0.450	L	0.350	0.400	0.450
L1	0.075 REF			L2	0.05 REF		
ϕ	0.150	0.200	0.250				

REEL SPECIFICATION

P/N	PKG	QTY
TPD4EUSB30DQAR-MS	DFN2510-10	3000

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.